

# Thermal Model Generation and Analysis of the MDC22GCMG-67E0 Multiple Device Canopy

## Baseline Results

Legacy Electronics

Project: TDSW130509-01

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# Objectives

- **To build a Computational Fluid Dynamics FloTHERM® model of Legacy Electronics' MDC22GCMG-67E0 multiple device canopy, and simulate the package when mounted in a JEDEC Still-Air test environment.**
  - Power Dissipation
    - Total Power:  $0.36 \text{ Watts/device} \times 2 = 0.72 \text{ W}$
  - Air-Flow Environment
    - Free Convection

# JEDEC Still-Air Test Environment

Ambient Temperature: 20 °C

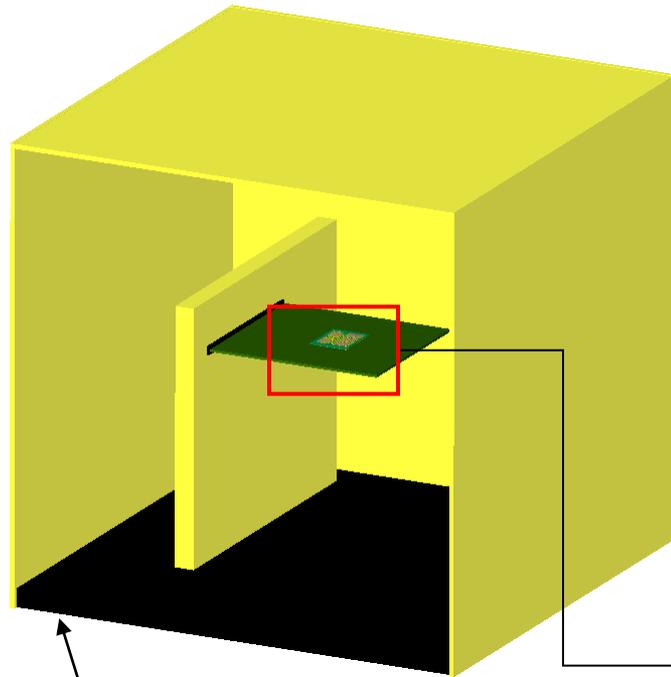
Elevation: Sea Level

Enclosure Dimensions (in): 12 X 12 X 12

Jedec Board Dimensions (mm): 114.5 X 101.6 X 1.6

Jedec Board Dielectric: FR4

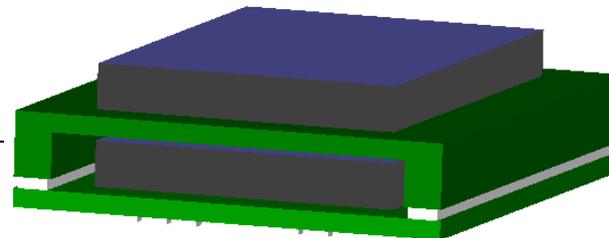
Jedec Board Metal: Cu



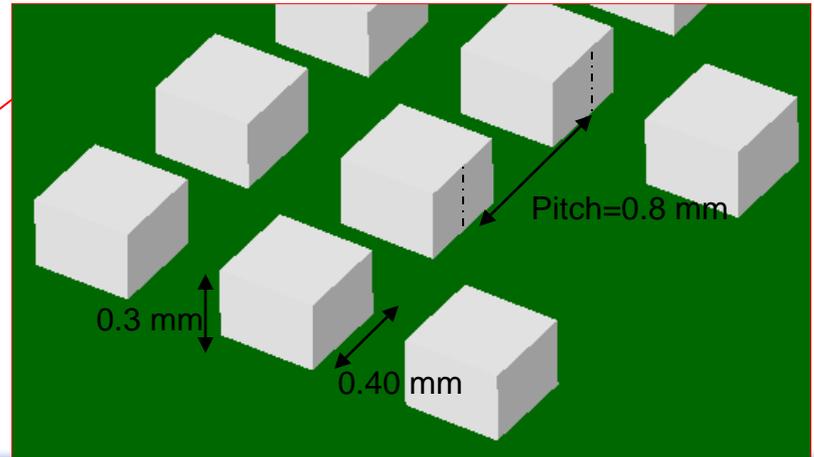
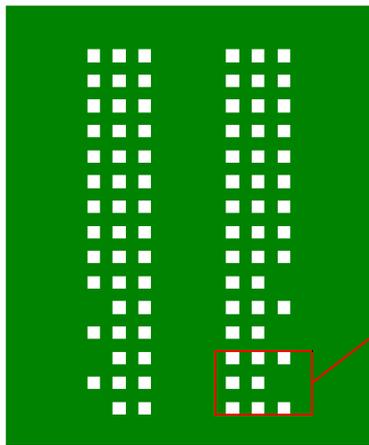
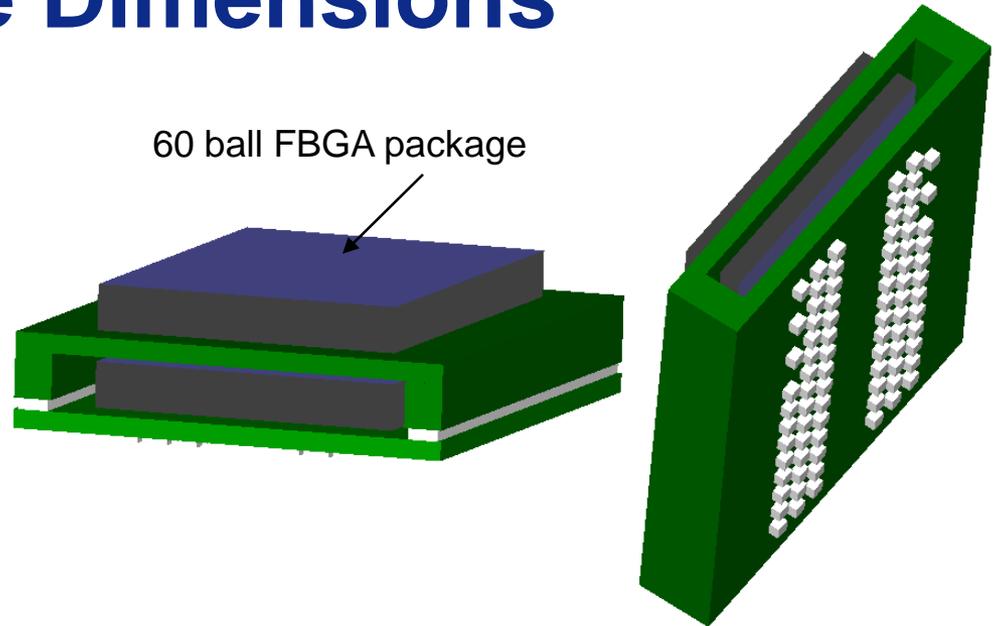
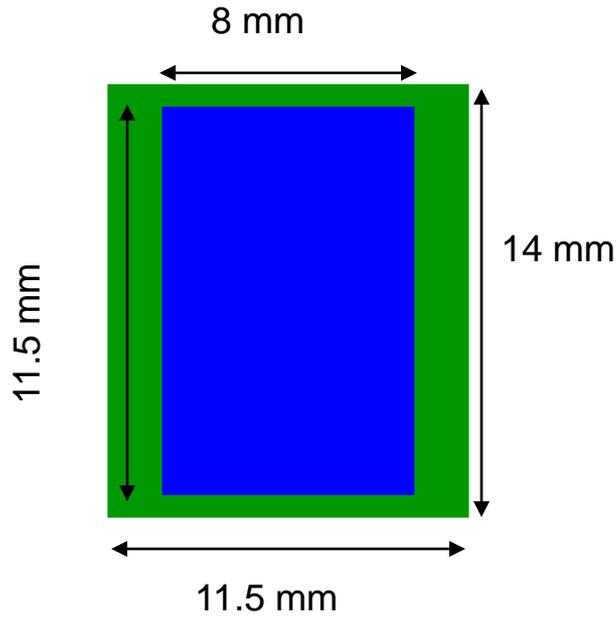
Wall hidden for clarity

## Jedec Board Stackup

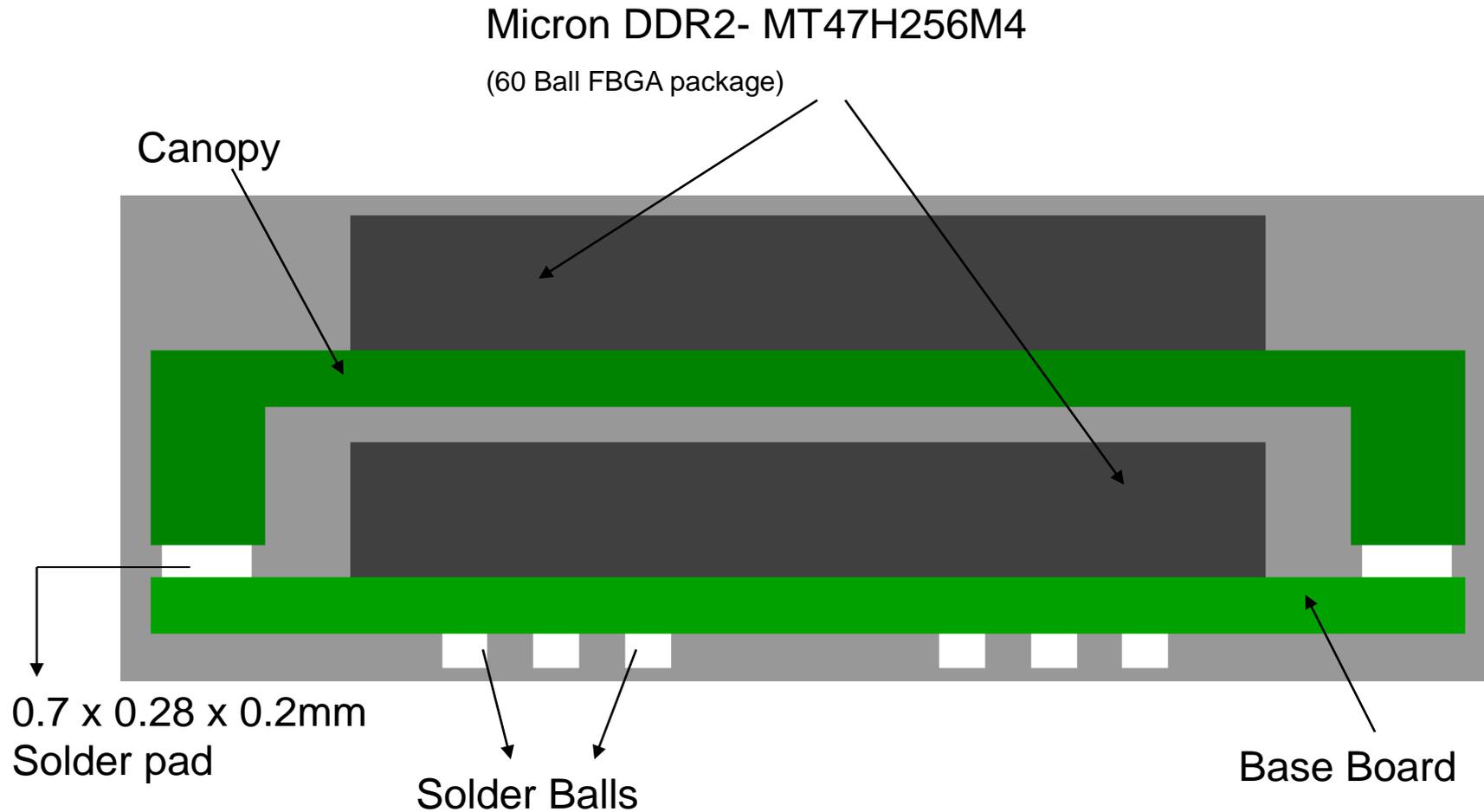
Trace	Thickness (oz)	% Cu
1	2	20
2	1	90
3	1	90
4	2	20



# Package Dimensions

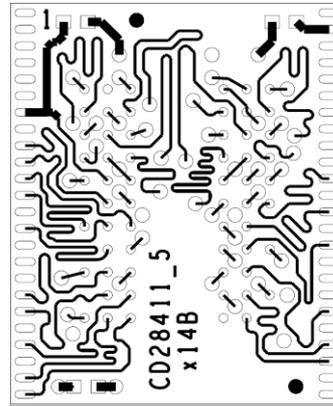


# MDC22GCMG-67E0 Stackup

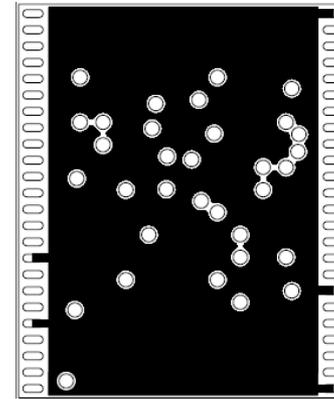


# Base Board Layer Detail

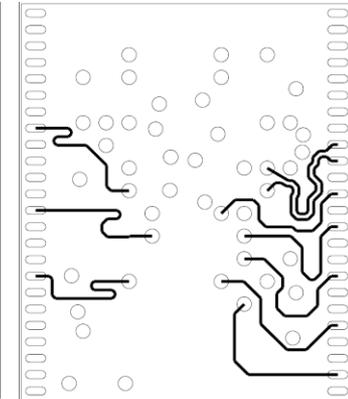
Layer	Type	Thickness (Oz)	Coverage (%)
1	Signal	1	17%
2	Ground	1	74%
3	Signal	1	6%
4	Signal	1	7%
5	Power	1	73%
6	Signal	1	16%



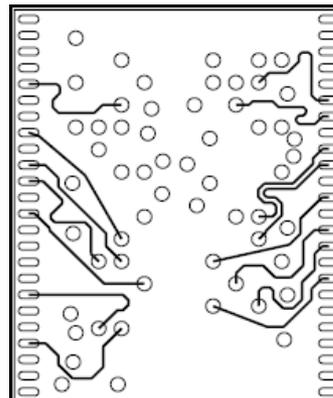
Layer 1



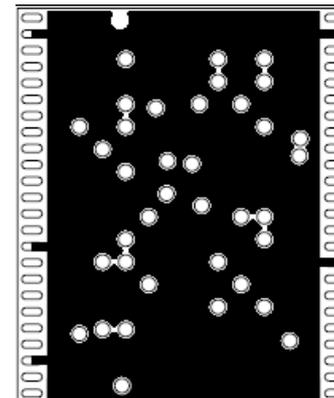
Layer 2



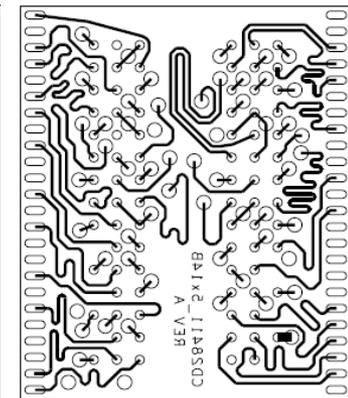
Layer 3



Layer 4



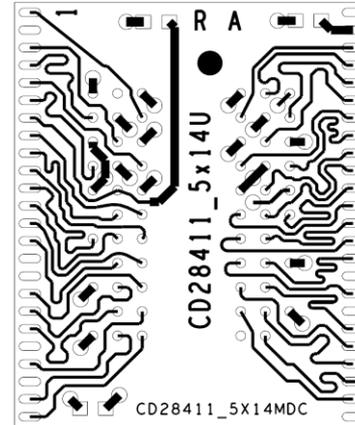
Layer 5



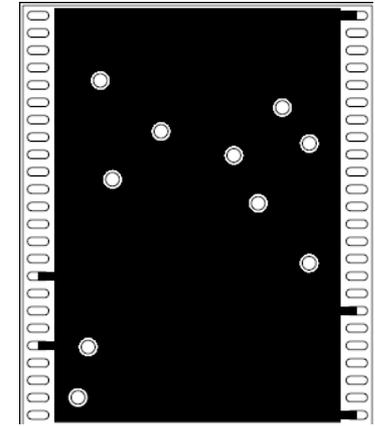
Layer 6

# Canopy Layer Detail

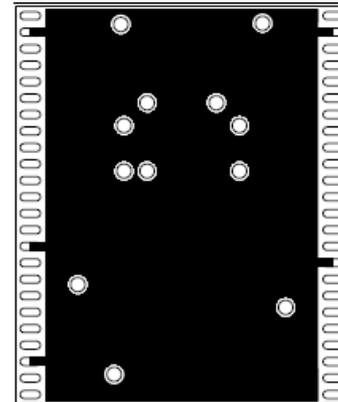
Layer	Type	Thickness (Oz)	Coverage (%)
1	Signal	1	20%
2	Ground	1	80%
3	Power	1	79%
4	Signal	1	1%



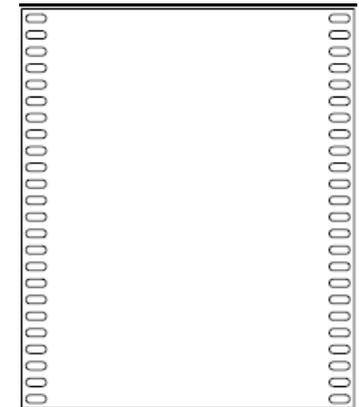
Layer 1



Layer 2



Layer 3



Layer 4

# Material Properties

	Material	Conductivity (W/mK)
Prepreg	FR4	0.3
Traces	Cu	384
Solder	Solder (Sn96.5% and Ag3.5 %)	78.4

- The in-plane conductivities of layers are calculated as average of Cu and FR4 depending on % coverage.
- The Solder properties were obtained from FloTHERM Library with 96.5% Sn and 3.5% Ag.

# Via and Solder Pad Details

- Similar to the layer definition seen in slides 6 and 7, the vias and canopy solder pads are modeled as rectangular blocks with volume weighted thermal conductivity.
- A summary of the thermal conductivities are seen below.
- Detailed calculations are available upon request

Rail Vias		
outline area	14 mm <sup>2</sup>	
# of vias	24	
area of vias	0.75 mm <sup>2</sup>	5%
area of FR4	13.25 mm <sup>2</sup>	95%
<b>k_effective</b>	<b>7.76 W/mK</b>	

Lower Board Top-L3		
outline area	161 mm <sup>2</sup>	
# of vias	48	
area of vias	1.51 mm <sup>2</sup>	1%
area of FR4	159.49 mm <sup>2</sup>	99%
<b>k_effective</b>	<b>1.60 W/mK</b>	

Lower Board L4-Bottom		
outline area	161 mm <sup>2</sup>	
# of vias	58	
area of vias	1.82 mm <sup>2</sup>	1%
area of FR4	159.18 mm <sup>2</sup>	99%
<b>k_effective</b>	<b>1.97 W/mK</b>	

Solder Pads		
outline area	9.8 mm <sup>2</sup>	
solderball area	0.18 mm <sup>2</sup>	
# of solderballs	24	
total solder area	4.30 mm <sup>2</sup>	44%
area of air	5.50 mm <sup>2</sup>	56%
<b>k_effective</b>	<b>34.42 W/mK</b>	

Canopy L3-Bottom		
outline area	161 mm <sup>2</sup>	
# of vias	58	
area of vias	1.82 mm <sup>2</sup>	1%
area of FR4	159.18 mm <sup>2</sup>	99%
<b>k_effective</b>	<b>1.87 W/mK</b>	

Canopy Top-L3		
outline area	161 mm <sup>2</sup>	
# of vias	34	
area of vias	1.07 mm <sup>2</sup>	1%
area of FR4	159.93 mm <sup>2</sup>	99%
<b>k_effective</b>	<b>1.22 W/mK</b>	

# DDR2: 2-Resistor model

- The DRAM's are modeled as a two resistor compact thermal models. The values for Junction-to-Board thermal resistance ( $\theta_{JB}$ ) and Junction-to-Case thermal resistance ( $\theta_{JC}$ ) were extracted from Micron Data Sheet.

**Table 7: Thermal Impedance**

Die Revision	Package	Substrate	$\theta_{JA}$ ( $^{\circ}\text{C/W}$ ) Airflow = 0m/s	$\theta_{JA}$ ( $^{\circ}\text{C/W}$ ) Airflow = 1m/s	$\theta_{JA}$ ( $^{\circ}\text{C/W}$ ) Airflow = 2m/s	$\theta_{JB}$ ( $^{\circ}\text{C/W}$ )	$\theta_{JC}$ ( $^{\circ}\text{C/W}$ )
E <sup>1</sup>	60-ball	2-layer	56.7	42.1	36.8	22.7	2.5
		4-layer	40.2	32.8	29.9	22.1	

# Operating Temperature Limits

- According to the datasheet published by the DRAM manufacturer (Micron) the maximum DRAM operating temperatures are:
  - Commercial Temperature (IT):
    - $0^{\circ}\text{C} < T_{\text{case}} < 85^{\circ}\text{C}$

# Results

# Component Temperature Summary

DRAM	Tcase_predicted (°C)	*Tcase_max (°C)	Margin (°C)
top	<b>51.4</b>	85	33.6
bottom	<b>46.5</b>	85	38.5

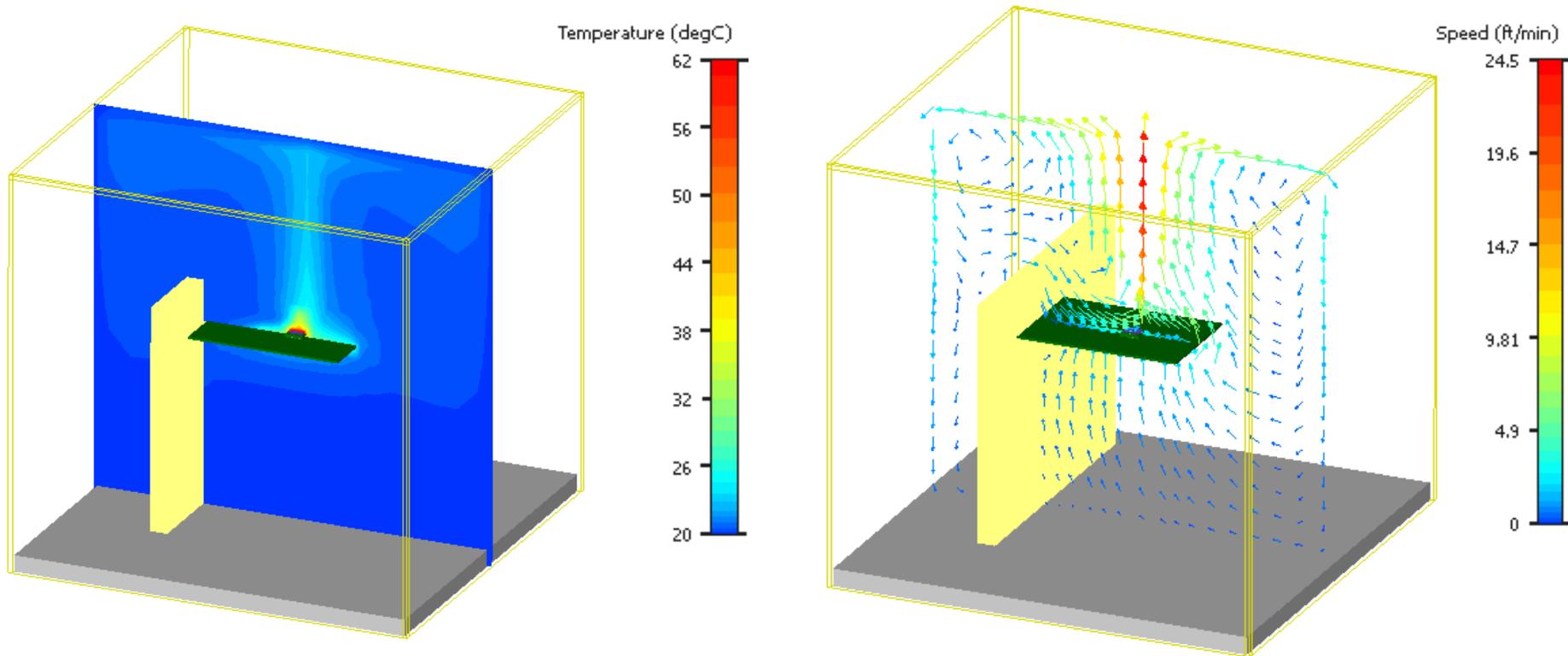
\* max junction temperature from Micron datasheet

DRAM	Tj_predicted (°C)	Tamb (°C)	Heat Diss (W)	Θja* (°C/W)
top	51.4	20.0	0.36	87.3
bottom	46.5	20.0	0.36	73.7

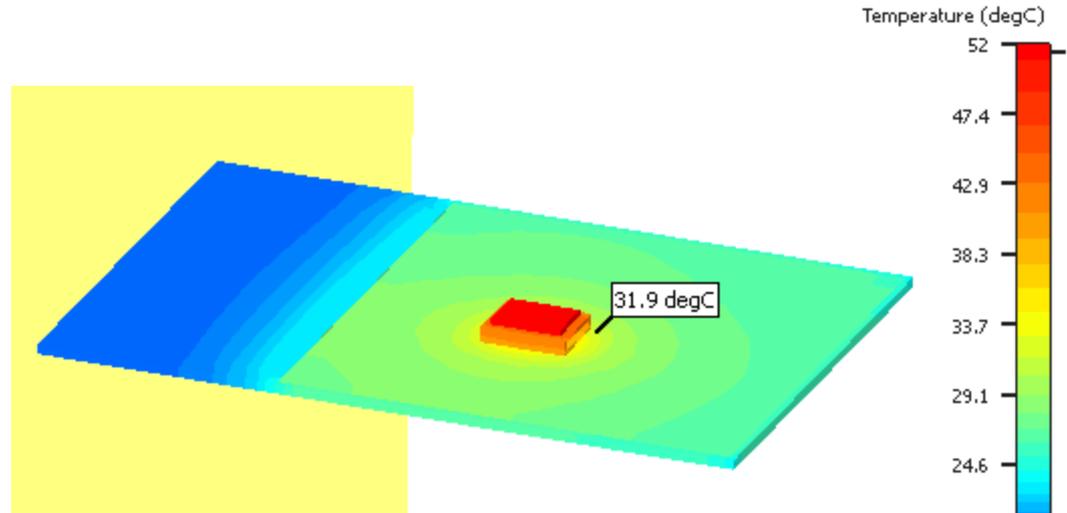
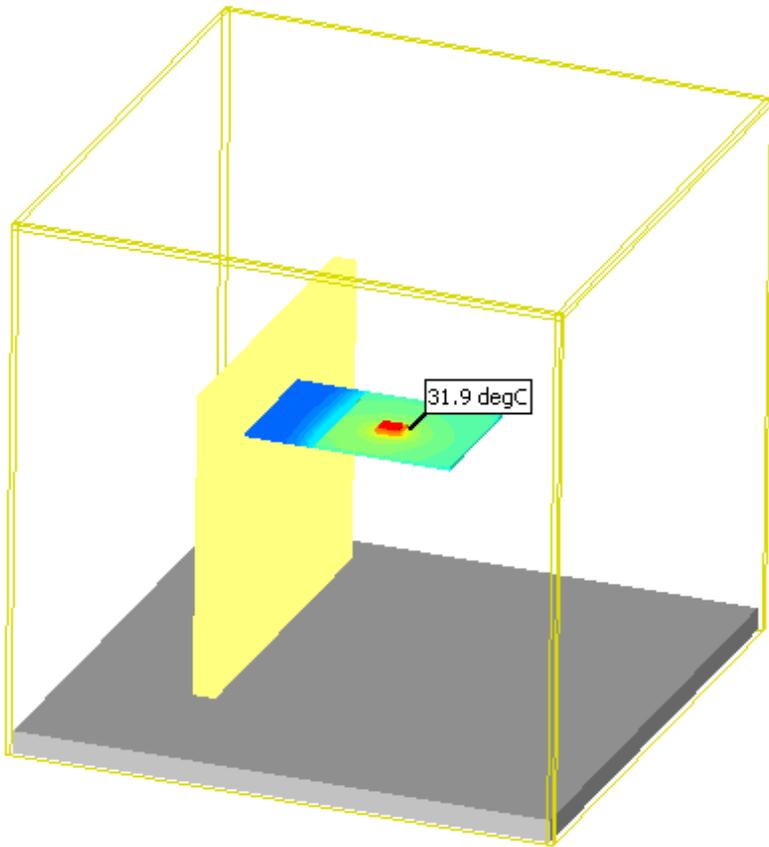
\* Junction-to-Ambient thermal resistance

# Air Temperature and Speed

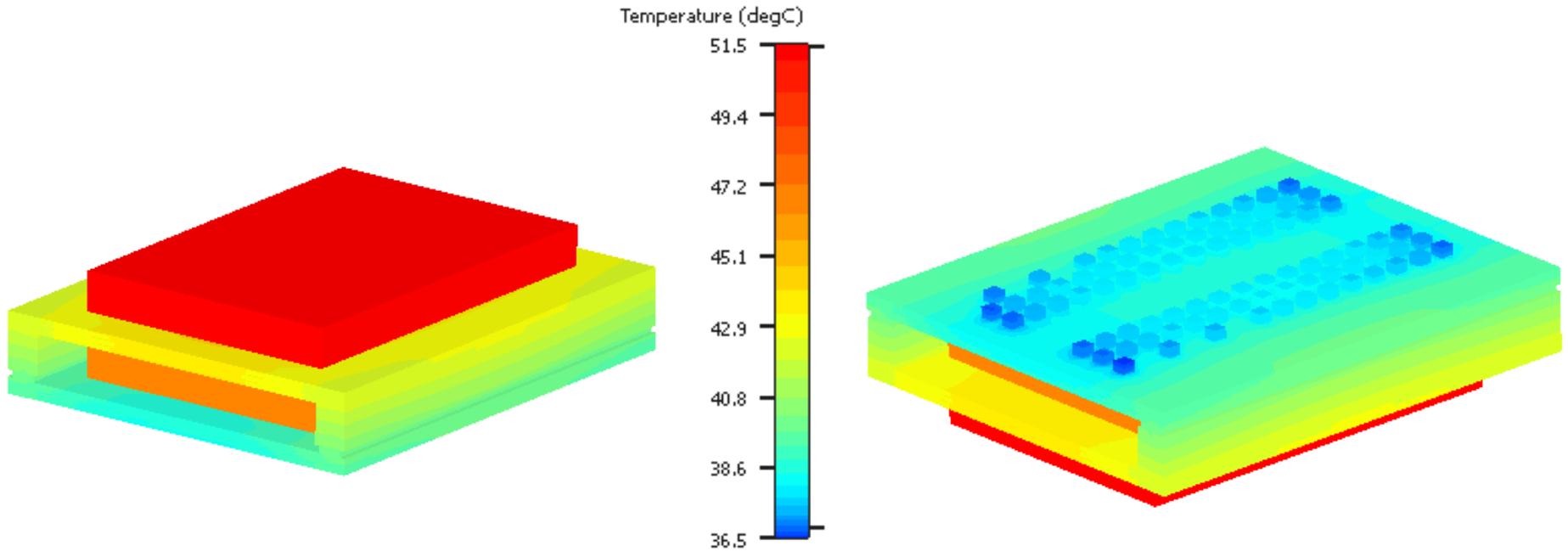
- Cutplane taken through centerline of the package



# Host Board Surface Temperature



# Component Surface Temperature



# Summary

- A Computational Fluid Dynamics, FloTHERM® model of Legacy Electronics' **MDC22GCMG-67E0 multiple device canopy** has been created. The device has been equipped with 2 Micron DDR2-MT47H256M4 memory chips, and simulated in a JEDEC JESD51-2A Still-Air test environment.
- The predicted case temperature of the memory chips are:
  - Top DRAM – 51.4 °C; 33.6 °C below the maximum operating temperature
  - Bottom DRAM – 46.5 °C; 38.5 °C below the maximum operating temperature
- The junction-to-ambient thermal resistance of the hottest DRAM is predicted to be ~ 87.3 °C/W